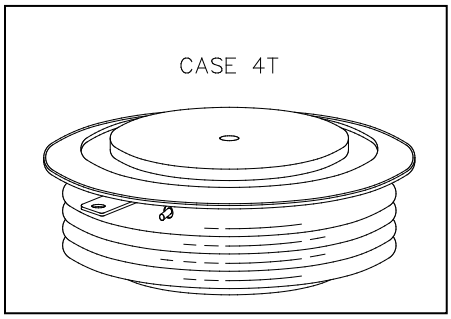
HIGH POWER THYRISTOR FOR PHASE CONTROL APPLICATIONS

KK1000A2000V
C712L



Features:

- . All Diffused Structure
- . Center Amplifying Gate Configuration
- . Blocking capabilty up to 2100 volts
- . Guaranteed Maximum Turn-Off Time
- . High dV/dt Capability
- . Pressure Assembled Device

ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
2000	2000	2100

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state	I_{RRM} / I_{DRM}	20 mA 90 mA (3)
Critical rate of voltage rise	dV/dt (4)	500 V/μsec

Notes:
All ratings are specified for Tj=25 °C unless otherwise stated.
(1) All voltage ratings are specified for an applied 50Hz/60zHz sinusoidal waveform over the temperature range -40 to +125 °C.
(2) 10 msec. max. pulse width
(3) Maximum value for Tj = 125 °C.
(4) Minimum value for linear and exponential waveshape to 80% rated V_{DRM}. Gate open. Tj = 125 °C.
(5) Non-repetitive value.
(6) The value of di/dt is established in accordance with EIA/NIMA Standard RS-397, Section 5-2-2-6. The value defined would be in addition to that obtained from a snubber circuit, comprising a 0.2 μF capacitor and 20 ohms resistance in parallel with the thristor under test.

Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average value of on-state current	$I_{T(AV)}$		1000		A	Sinewave,180° conduction,T_c=80°C
RMS value of on-state current	I_{TRMS}		1570		A	Nominal value
Peak one cPSTCle surge (non repetitive) current	I_{TSM}		- 18500		A A	8.3 msec (60Hz), sinusoidal wave-shape, 180° conduction, T_j = 125 °C 10.0 msec (50Hz), sinusoidal wave- shape, 180° conduction, T_j = 125 °C
I square t	I^2t		$1.66x10^6$		A^2s	8.3 msec and 10.0 msec
Latching current	I_L		-		mA	V_D = 24 V; R_L= 12 ohms
Holding current	I_H		-		mA	V_D = 24 V; I = 2.5 A

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Peak on-state voltage	V_{TM}		1.45		V	I_{TM} = 1000 A; Duty Cycle ≤ 0.01%; T_j =1 25 °C
Critical rate of rise of on-state current (5, 6)	di/dt		800		A/μs	Switching from V_{DRM} ≤ 1000 V, non-repetitive
Critical rate of rise of on-state current (6)	di/dt		200		A/μs	Switching from V_{DRM} ≤ 1000 V

ELECTRICAL CHARACTERISTICS AND RATINGS

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		100		W	t_p = 40 us
Average gate power dissipation	$P_{G(AV)}$		5		W	
Peak gate current	I_{GM}		-		A	
Gate current required to trigger all units	I_{GT}		- 120 -		mA mA mA	V_D = 6 V;R_L = 3 ohms;T_j = -40 °C V_D = 6 V;R_L = 3 ohms;T_j = +25 °C V_D = 6 V;R_L = 3 ohms;T_j = +125°C
Gate voltage required to trigger all units	V_{GT}		- 3.0 -		V V V	V_D = 6 V;R_L = 3 ohms;T_j = -40 °C V_D = 6 V;R_L = 3 ohms;T_j = 0-125°C V_D = Rated V_{DRM}; R_L = 1000 ohms; T_j = + 125 °C
Peak negative voltage	V_{GRM}		20		V	

Dynamic

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Delay time	t_d		-	0.7	μs	I_{TM} = 50 A; V_D = Rated V_{DRM} Gate pulse: V_G = 20 V; R_G = 20 ohms; t_r = 0.1 μs; t_p = 20 μs
Turn-off time (with V_R = -50 V)	t_q		-	50	μs	I_{TM} = 1000 A; di/dt = 25 A/μs; V_R ≥ -50 V; Re-applied dV/dt = 20 V/μs linear to 80% V_{DRM}; V_G = 0; T_j = 125 °C; Duty cPSTCle ≥ 0.01%
Reverse recovery charge	Q_{rr}		*		μC	I_{TM} = 1000 A; di/dt = 25 A/μs; V_R ≥ -50 V

* For guaranteed max. value, contact factory.

THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T_j	-40	+125		°C	
Storage temperature	T_{stg}	-40	+125		°C	

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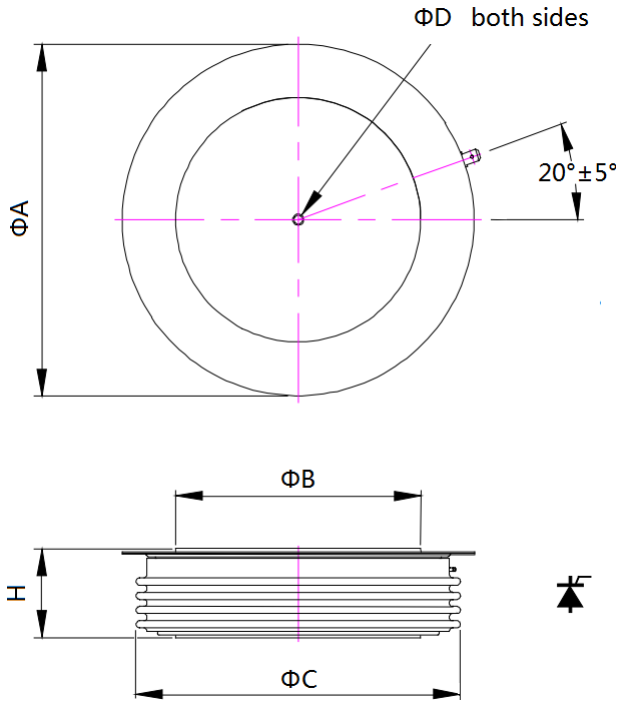
Thermal resistance - junction to case	$R_{\Theta (j-c)}$		0.023 -		°C/W	Double sided cooled Single sided cooled
Thermal resistamce - case to sink	$R_{\Theta (c-s)}$		0.0075 -		°C/W	Double sided cooled * Single sided cooled *
Mounting force	P	22.2	26.6		kN	
Weight	W			-	g	About

* Mounting surfaces smooth, flat and greased

CASE OUTLINE AND DIMENSIONS



Sym	A	B	C	D	H
mm	75	47	66	3.5×3	26±1

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